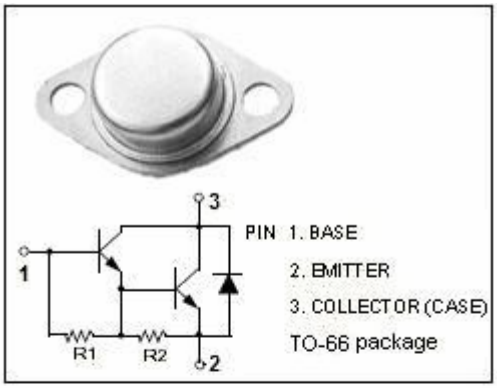
isc Silicon NPN Darlingtion Power Transistor 2SD692

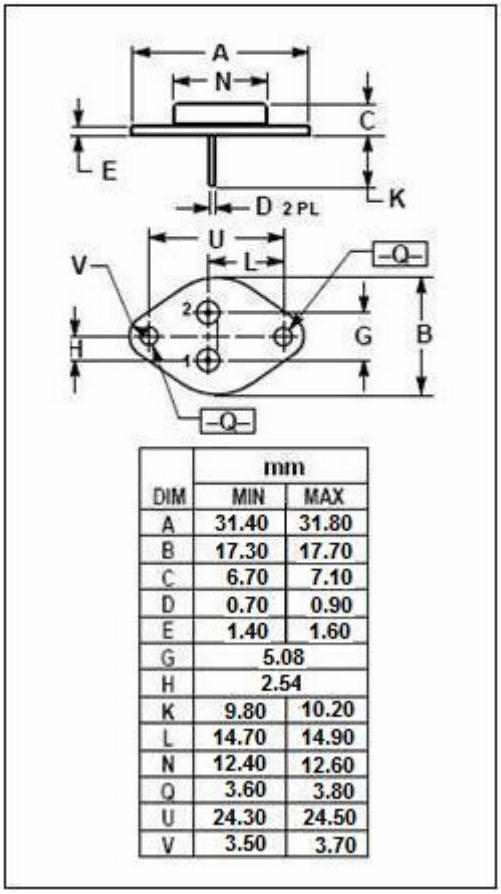
DESCRIPTION

- Built-in Base-Emitter Shunt Resistors
- High DC current gain-
  h_{FE} = 1000 (Min) @ I_C =1 Adc
- Collector-Emitter Breakdown Voltage-
  $V_{(BR)CEO}$= 80V(Min)
- Wide Area of Safe Operation



APPLICATIONS

- Designed for high power amplifier applications.



DIM	mm MIN	MAX
A	31.40	31.80
B	17.30	17.70
C	6.70	7.10
D	0.70	0.90
E	1.40	1.60
G	5.08	
H	2.54	
K	9.80	10.20
L	14.70	14.90
N	12.40	12.60
Q	3.60	3.80
U	24.30	24.50
V	3.50	3.70

ABSOLUTE MAXIMUM RATINGS(T_C=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	100	V
V_{CER}	Collector-Emitter Voltage	100	V
V_{CEO}	Collector-Emitter Voltage	80	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current -Continuous	6	A
I_B	Base Current -Continuous	3	A
P_C	Collector Power Dissipation@T_C=25℃	50	W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-65~150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 50mA ; I_B= 0	80		V
V_{CER}	Collector-Emitter Breakdown Voltage	I_C= 50mA ; R_{BE}= 1 kΩ	100		V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 3A; I_B= 60mA		1.7	V
I_{CBO}	Collector Cutoff current	V_{CB}= 100V; I_E=0		10	μA
I_{EBO}	Emitter Cut-off current	V_{EB}= 6V; I_C= 0		10	mA
h_{FE}	DC Current Gain	I_C= 1A ; V_{CE}= 4V	1000	10000	

◆ **h_{FE} Classifications**

Q	P	O
1000-2500	2000-5000	4000-10000